

VERSION WITHOUT MARKINGS

PLEASE AMEND CLAIMS 34, 35, and 38 (UNMARKED VERSION):

C.1

34. (AMENDED 2X) A bond pad structure, comprising:

- a semiconductor substrate;
- a plurality of conductive regions formed over said semiconductor substrate;
- a passivating layer formed over said conductive regions, having multiple openings to each conductive region;
- a barrier layer formed over said passivating layer and in said openings;
- a conducting bond pad formed over each said conductive region and over said barrier layer, whereby an upper surface of said conductive bond pad provides added adhesion for subsequently formed bonds.

35. (AMENDED 2X) The bond pad structure of Claim 34, wherein said conducting bond pad is formed of copper.

C.2

38. (AMENDED 2X) The bond pad structure of Claim 34, wherein said conducting bond pad is formed of aluminum.